

MOSFETs Silicon N-Channel MOS

# **SSM6N357R**

### 1. Applications

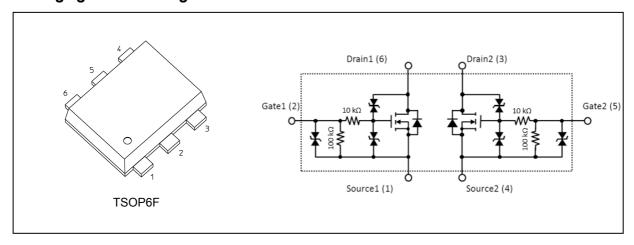
· Relay Drivers

#### 2. Features

- (1) AEC-Q101 qualified (Note 1)
- (2) 3.0-V gate drive voltage.
- (3) Built-in Internal Zener diodes and resistors.
- (4) HBM: 2-kV class

Note 1: For detail information, please contact to our sales.

### 3. Packaging and Pin Assignment





## 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25$ °C)

| Characteristics               |           |                    | Symbol           | Rating     | Unit |
|-------------------------------|-----------|--------------------|------------------|------------|------|
| Drain-source voltage          |           |                    | V <sub>DSS</sub> | 60         | V    |
| Gate-source voltage           |           |                    | $V_{GSS}$        | ±12        |      |
| Drain current (DC)            |           | (Note 1)           | I <sub>D</sub>   | 650        | mA   |
| Drain current (pulsed)        |           | (Note 1), (Note 2) | I <sub>DP</sub>  | 1300       |      |
| Power dissipation             |           | (Note 3)           | P <sub>D</sub>   | 1          | W    |
| Power dissipation             | (t ≤ 10s) | (Note 3)           | P <sub>D</sub>   | 1.5        |      |
| Channel temperature           |           |                    | T <sub>ch</sub>  | 150        | °C   |
| Single-pulse avalanche energy |           | (Note 4)           | E <sub>AS</sub>  | 12.6       | mJ   |
| Storage temperature           |           |                    | T <sub>stg</sub> | -55 to 150 | ç    |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Pulse width (PW)  $\leq$  10  $\mu$ s, duty  $\leq$  1 %
- Note 3: Device mounted on an FR4 board. (25.4 mm × 25.4 mm × 1.6 mm, Cu pad: 645 mm<sup>2</sup>)
- Note 4:  $V_{DD}$  = 25 V,  $T_{ch}$  = 25 °C (Initial state), L = 20 mH

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.



#### 5. Electrical Characteristics

### 5.1. Static Characteristics (Unless otherwise specified, Ta = 25 °C)

| Characteristics                |          | Symbol               | Test Condition                                   | Min | Тур. | Max | Unit |
|--------------------------------|----------|----------------------|--|-----|------|-----|------|
| Gate leakage current           |          | I <sub>GSS</sub>     | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 3 \text{ V}$ | _   | _    | ±60 | μА   |
|                                |          |                      | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 5 \text{ V}$ | _   | _    | ±90 |      |
| Drain cut-off current          |          | I <sub>DSS</sub>     | V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 0 V    | _   | _    | 0.5 |      |
|                                |          |                      | V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V    | _   | _    | 1   |      |
| Drain-source breakdown voltage |          | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V    | 60  |      |     | V    |
| Gate threshold voltage         | (Note 1) | V <sub>th</sub>      | $V_{DS} = V_{GS}$ , $I_D = 1 \text{ mA}$         | 1.3 | _    | 2.0 |      |
| Drain-source on-resistance     | (Note 2) | R <sub>DS(ON)</sub>  | I <sub>D</sub> = 150 mA, V <sub>GS</sub> = 3 V   | _   | 1.2  | 2.4 | Ω    |
|                                |          |                      | I <sub>D</sub> = 150 mA, V <sub>GS</sub> = 5 V   | _   | 0.8  | 1.8 |      |
| Forward transfer admittance    | (Note 2) | Y <sub>fs</sub>      | V <sub>DS</sub> = 12 V, I <sub>D</sub> = 150 mA  | _   | 500  | _   | mS   |

Note 1: Let V<sub>th</sub> be the voltage applied between gate and source that causes the drain current (I<sub>D</sub>) to below (1 mA for this device). Then, for normal switching operation, V<sub>GS(ON)</sub> must be higher than V<sub>th</sub>, and V<sub>GS(OFF)</sub> must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ . Take this into consideration when using the device.

Note 2: Pulse measurement.

#### 5.2. Dynamic Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

| Characteristics                |          | Symbol           | Test Condition                                     | Min | Тур. | Max | Unit |
|--------------------------------|----------|------------------|--|-----|------|-----|------|
| Input capacitance              |          | C <sub>iss</sub> | $V_{DS} = 12 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , | _   | 43   | 60  | pF   |
| Reverse transfer capacitance   |          | C <sub>rss</sub> | f = 1 MHz  | _   | 2.5  | _   |      |
| Output capacitance             |          | C <sub>oss</sub> |  | _   | 20   | _   |      |
| Switching time (turn-on time)  | (Note 1) | t <sub>on</sub>  | $V_{DD}$ = 12 V, $V_{GS}$ = 0 to 3.0 V,            | _   | 990  | _   | ns   |
| Switching time (turn-off time) | (Note 1) | t <sub>off</sub> | $R_G = 50 \Omega$                                  | _   | 3000 | _   |      |

Note 1: See Chapter 5.3

### 5.3. Switching Time Test Circuit

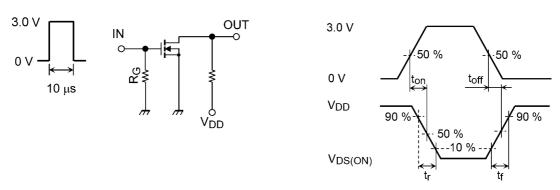


Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform

### 5.4. Gate Charge Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

| Characteristics                                 | Symbol           | Test Condition                     | Min | Тур. | Max | Unit |
|---|------------------|------------------------------------|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg               | $V_{DD}$ = 12 V, $I_{D}$ = 650 mA, | _   | 1.5  |     | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> | V <sub>GS</sub> = 5.0 V            | _   | 0.2  |     |      |
| Gate-drain charge                               | $Q_{gd}$         |                                    | _   | 1.2  |     |      |

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### 5.5. Source-Drain Characteristics (Unless otherwise specified, Ta = 25 °C)

| Characteristics       |          | Symbol    | Test Condition                                  | Min | Тур.  | Max  | Unit |
|-----------------------|----------|-----------|---|-----|-------|------|------|
| Diode forward voltage | (Note 1) | $V_{DSF}$ | I <sub>D</sub> = -650 mA, V <sub>GS</sub> = 0 V | _   | -0.87 | -1.2 | V    |

Note 1: Pulse measurement.

### 6. Marking

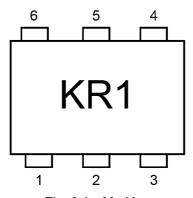


Fig. 6.1 Marking



### 7. Characteristics Curves (Note)

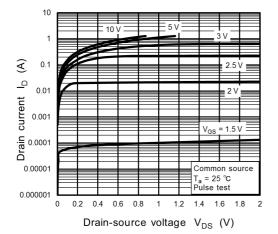


Fig. 7.1 I<sub>D</sub> - V<sub>DS</sub>

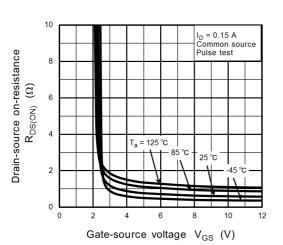


Fig. 7.3 R<sub>DS(ON)</sub> - V<sub>GS</sub>

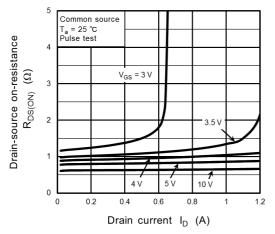


Fig. 7.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

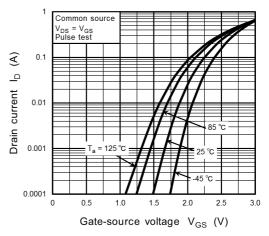


Fig. 7.2 I<sub>D</sub> - V<sub>GS</sub>

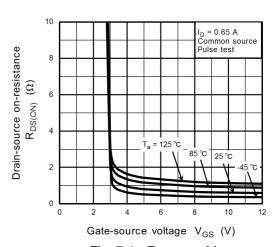


Fig. 7.4 R<sub>DS(ON)</sub> - V<sub>GS</sub>

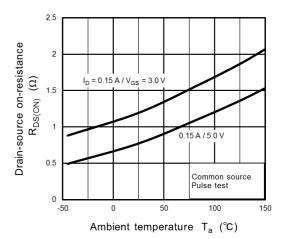
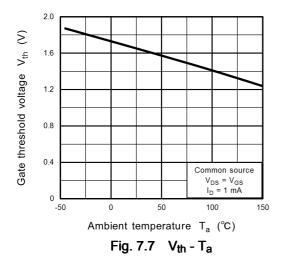
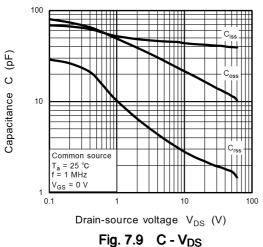
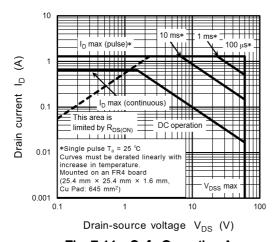


Fig. 7.6 R<sub>DS(ON)</sub> - T<sub>a</sub>











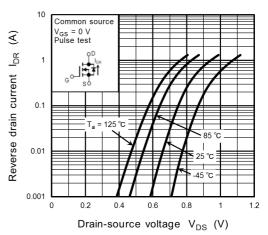


Fig. 7.8 IDR - VDS

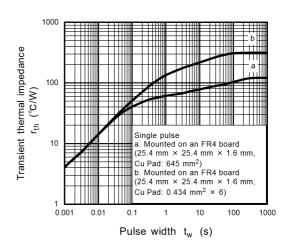


Fig. 7.10 rth - tw

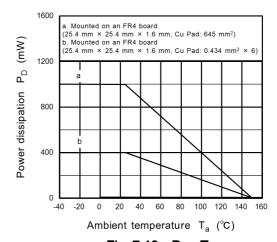


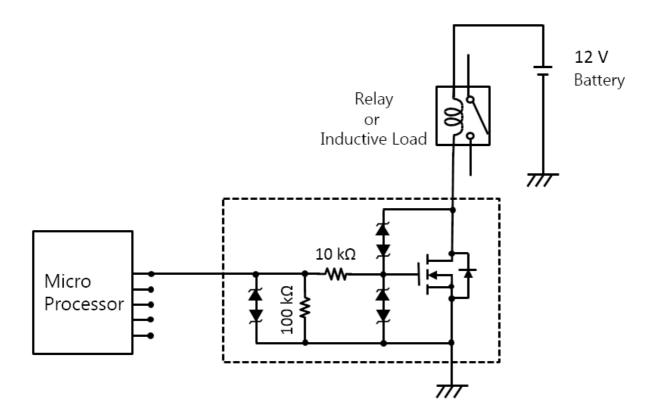
Fig. 7.12 P<sub>D</sub> - T<sub>a</sub>

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Rev.3.0



### 8. Application Information

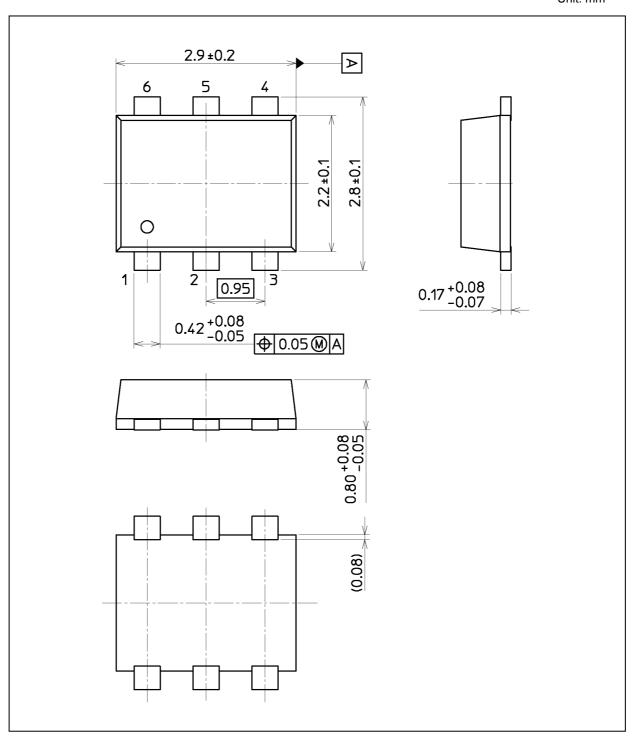


Rev.3.0



### **Package Dimensions**

Unit: mm



Weight: 0.016 g (typ.)

|                  | Package Name(s) |
|------------------|-----------------|
| Nickname: TSOP6F |                 |



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**Телефон:** 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: <u>org@eplast1.ru</u>

Адрес: 198099, г. Санкт-Петербург, ул. Калинина,

дом 2, корпус 4, литера А.